

LECTURE - 8

INTRINSIC SEMICONDUCTOR

AT EQUILIBRIUM

$$n_0 = p_0 = n_i$$

} TEMPERATURE
DEPENDENT

→ EHP GENERATION

→ ONLY THERMAL
EXCITATION

EXTRINSIC

→ DONOR ATOMS → N_d DONORS
↓
#/cm³

THIS APPROX.
SHOULD NOT
BE USED TO CALCULATE
EXACT CONCENTRATION!

$$n_0 \approx N_d$$

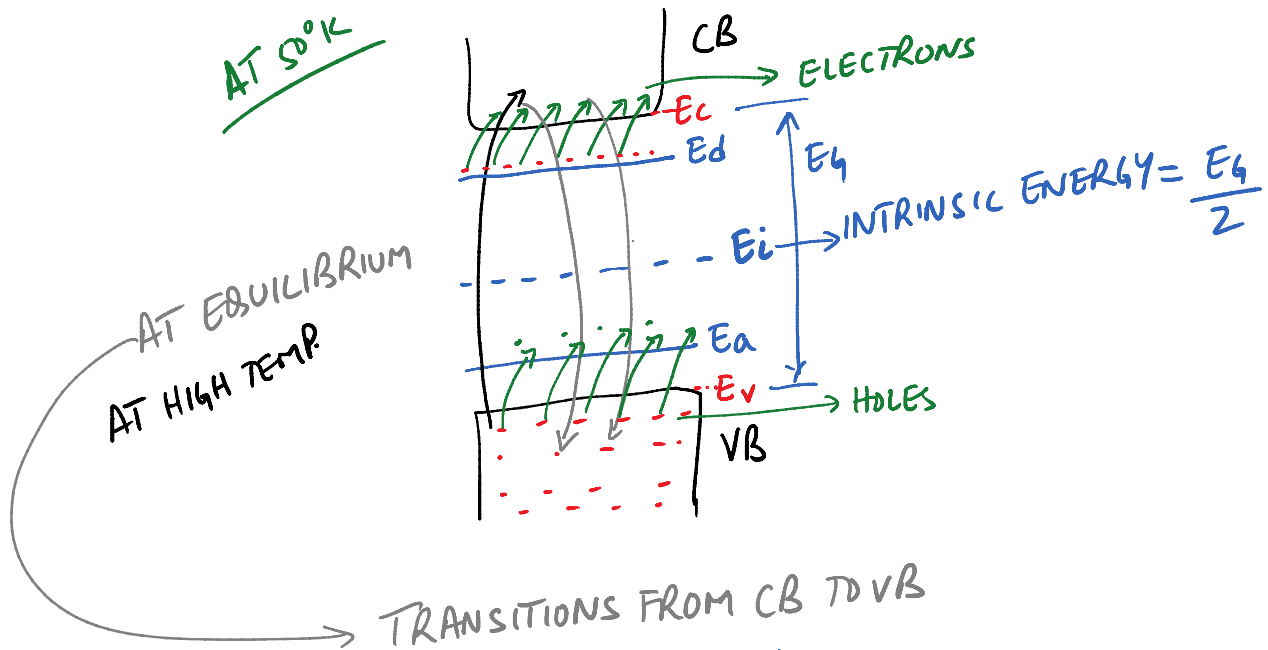
n-TYPE SEMICONDUCTOR

→ ACCEPTOR ATOMS → N_a ACCEPTORS
↓
#/cm³

$$p_0 \approx N_a$$

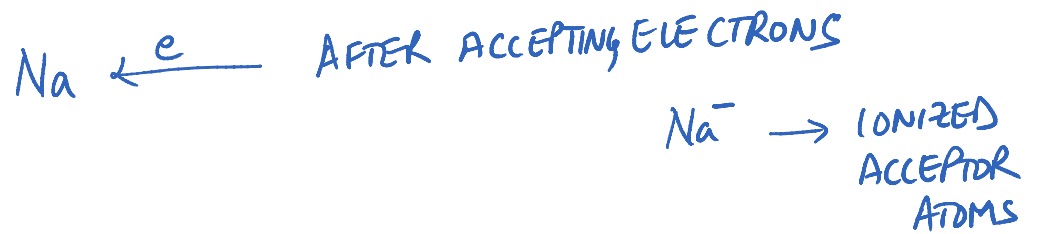
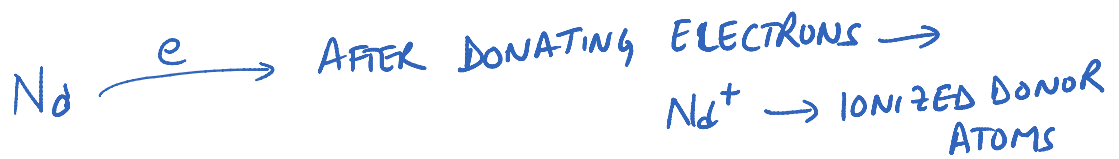
p-TYPE SEMICONDUCTOR

IF BOTH ACCEPTORS AND DONORS PRESENT



EXAMPLE

$N_d > N_a$
 \therefore NET # OF ELECTRONS = $N_d - N_a$



MATERIAL ITSELF IS ELECTROSTATICALLY
NEUTRAL

SUM OF POSITIVE CHARGES
{ HOLES + IONIZED DONOR ATOMS }

= SUM OF NEGATIVE CHARGES
{ ELECTRONS + IONIZED ACCEPTOR ATOMS }

$$P_0 + N_d^+ = n_0 + N_a^-$$

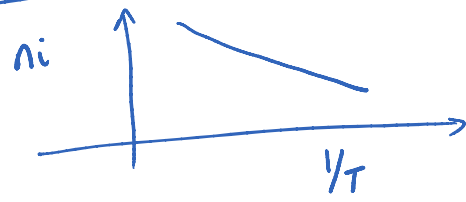
SAY EXAMPLE
MATERIAL IS HEAVILY DOPED WITH
DONORS (n-TYPE) ($n_0 > p_0$)
AND ALL IMPURITIES ARE IONIZED
 $n_0 \approx N_d - N_a$

TWO EQUATIONS

$$\begin{aligned} \textcircled{1} \quad n_0 + N_a^- &= p_0 + N_d^+ \\ \textcircled{2} \quad n_0 p_0 &= n_i^2 \end{aligned}$$

TEMPERATURE DEPENDENCY

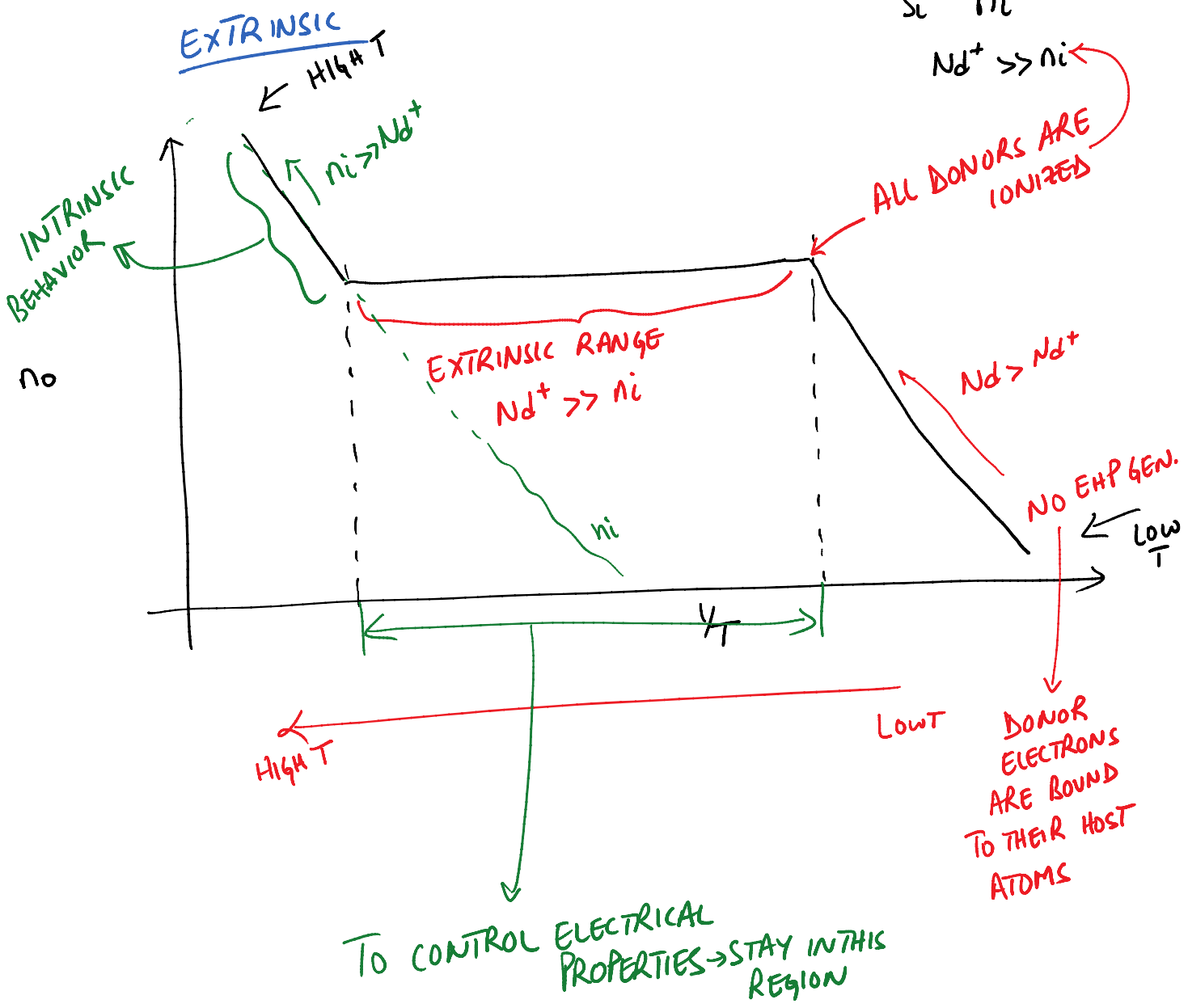
INTRINSIC



DOPING WITH DONORS

Si n_i

$N_d^+ \gg n_i$



* DOPED THE MATERIAL SUCH THAT THE EXTRINSIC RANGE EXTENDS BEYOND THE HIGHEST OPERATING TEMPERATURE!